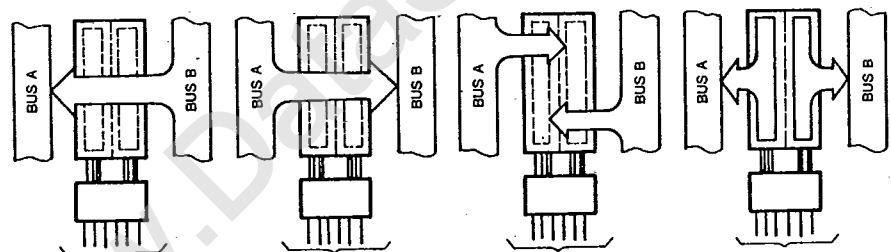
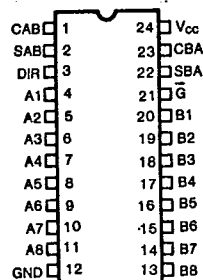


KS54AHCT 646/648
KS74AHCT
Octal 3-State Bus Transceivers
with Registers

T-52-31

FEATURES

- 8 bi-directional data paths
- Transmits direct or stored data in either direction
- 24-pin slim DIP package
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ($I_{OL} = 24 \text{ mA}$ @ $V_{OL} = 0.5\text{V}$) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over Industrial and military temperature ranges:
KS74AHCT: -40°C to $+85^{\circ}\text{C}$
KS54AHCT: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATION


(21)	(3)	(1)	(23)	(2)	(22)	(21)	(3)	(1)	(23)	(2)	(22)	(21)	(3)	(1)	(23)	(2)	(22)	(21)	(3)	(1)	(23)	(2)	(22)
G	DIR	CAB	CBA	SAB	SBA	G	DIR	CAB	CBA	SAB	SBA	G	DIR	CAB	CBA	SAB	SBA	G	DIR	CAB	CBA	SAB	SBA
L	L	X	X	X	L	L	H	X	X	L	X	L	L	X	X	X	L	L	L	X	X	X	L
X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X	X
H	X	X	X	X	X	H	X	X	X	X	X	H	X	X	X	X	X	H	X	X	X	X	X
Real-Time transfer bus B to bus A						Real-Time transfer bus A to bus B						Storage from A AND/OR B						Transfer stored data to A AND/OR B					

DESCRIPTION

The '646 and '648 are bi-directional bus transceivers with D-type flip-flops and control circuitry to facilitate high speed multiplexed data transmission. The '646 transmits true data and the '648 transmits inverted data.

Data can be transmitted directly from one port to the other in either direction. It also can be stored in the flip-flops from either or both ports for subsequent transmission to the opposite port. Six control inputs govern the data flow:

G (output enable) when high, all outputs are disabled, isolating the A and B ports. When low, one port is enabled at a time as determined by the DIR pin.

DIR (direction control) disables A or B outputs permitting the pins to be used as inputs thus determining the direction of a data flow. When DIR=high, data flows from A to B.

SAB,SBA (data source AB and BA) determines whether data transmitted is from the data inputs or the registers associated with those inputs.

CAB,CBA (Clock AB and BA) clocks data from the A inputs and the B inputs, respectively, into their associated registers. Since the clocks are not gated with the **G** and DIR pins, data at the A and B pins can be clocked into the flip-flops at any time.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

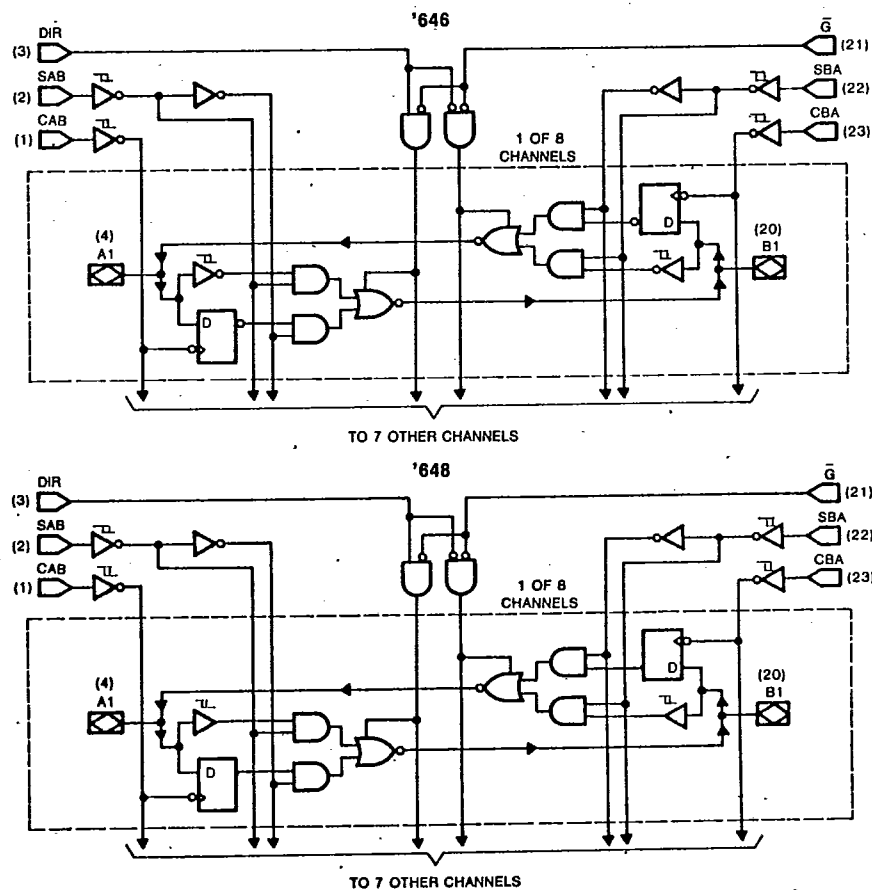


SAMSUNG SEMICONDUCTOR

KS54AHCT 646/648
KS74AHCT
Octal 3-State Bus Transceivers
with Registers
FUNCTION TABLE

Inputs						Data I/O*		Operation or Function	
$\bar{G}$	DIR	CAB	CBA	SAB	SBA	A1 thru A8	B1 thru B8	'646	'648
X	X	↑	X	X	X	Input	Input	Store A, B unspecified	Store A, B unspecified
X	X	X	↑	X	X	Not specified	Not specified	Store B, A unspecified	Store B, A unspecified
H	X	↑	↑	X	X	Input	Input	Store A and B data	Store A and B data
H	X	H or L	H or L	X	X	Input	Input	Isolation, hold storage	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-Time B data to A bus	Real-Time $\bar{B}$ data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus	Stored $\bar{B}$ data to A bus
L	H	X	X	L	X	Input	Output	Real-Time A data to B bus	Real-Time $\bar{A}$ data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus	Stored $\bar{A}$ data to B bus

*The data output functions may be enabled or disabled by various signals at the $\bar{G}$ and DIR inputs. Data input functions are always enabled, i.e., data at the bus pins will be stored on every low-to-high transition on the clock inputs.

LOGIC DIAGRAMS

SAMSUNG SEMICONDUCTOR

KS54AHCT 646/648
KS74AHCT
Octal 3-State Bus Transceivers
with Registers
Absolute Maximum Ratings*

Supply Voltage Range V_{CC} , -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 70 mA
 Continuous Current Through
 V_{CC} or GND pins ± 250 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_d † 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} ... 0V to V_{CC}
 Operating Temperature

Range KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

DC ELECTRICAL CHARACTERISTICS (V _{CC} = 5V ± 10%, unless otherwise specified)							
Characteristic	Symbol	Test Conditions	T _a = 25°C		KS74AHCT	KS54AHCT	Unit
			T _a = -40°C to +85°C		T _a = -55°C to +125°C		
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V _{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V _{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL} I _O =-20μA I _O =-6mA	V _{CC} 4.2	V _{CC} - 0.1 3.98	V _{CC} - 0.1 3.84	V _{CC} - 0.1 3.7	V
Maximum Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL} I _O =20μA I _O =12mA I _O =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I _{IN}	V _{IN} =V _{CC} or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I _{OZ}	Output Enable = V _{IH} V _{OUT} =V _{CC} or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND I _{OUT} =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI _{CC}	per input pin V _I =2.4V other Inputs: at V _{CC} or GND I _{OUT} =0μA		2.7	2.9	3.0	mA



KS54AHCT 646/648
KS74AHCT**Octal 3-State Bus Transceivers**
with Registers**AC ELECTRICAL CHARACTERISTICS** (Input $t_r, t_f \leq 2$ ns), AHCT646, AHCT648

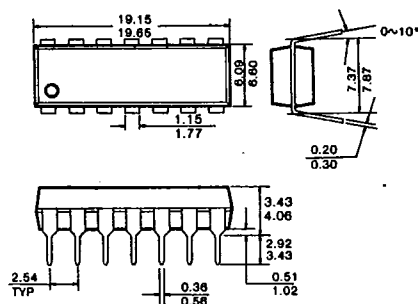
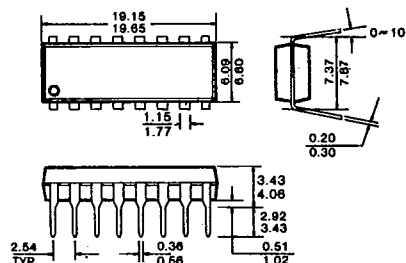
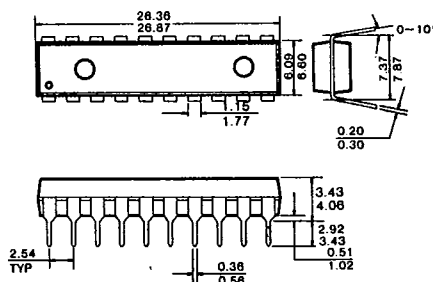
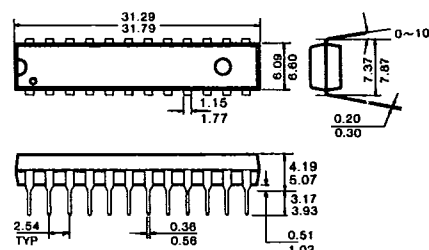
Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54AHCT $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Min	Max	Min	Max	
Maximum Frequency	$f_{\max}$	$C_L = 50\text{pF}$	45		30		25	MHz
Propagation Delay, A or B Input to B or A Output	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	11 14		18 23		22 28	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	11 14		18 23		22 28	
Propagation Delay, CBA or CAB Input to A or B Output	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18		25 30		30 36	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18		25 30		30 36	
Propagation Delay,†† SBA or SAB Input to A or B Output (with A or High)	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	16 19		27 33		32 38	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	16 19		27 33		32 38	
Propagation Delay,†† SBA or SAB Input to A or B Output (with A or Low)	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18		25 30		30 36	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18		25 30		30 36	
Out Enable Time, $\bar{G}$ or DIR Input to A or B Output	t_{PZH}	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$ $C_L = 150\text{pF}$	14 17		22 27		26 32	ns
	t_{PZL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	14 17		22 27		26 32	
Output Disable Time, $\bar{G}$ or DIR Input to A or B Output	t_{PHZ}	$R_L = 1\text{k}\Omega$	13		22		26	ns
	t_{PLZ}	$C_L = 50\text{pF}$	13		22		26	
Pulse Duration, Clocks High or low	t_w		8	12		15		ns
Set up Time, A before CAB† or B before CBA†	t_{su}		8	12		15		ns
Hold Time, A after CAB† or B after CBA†	t_h		-3	0		0		ns
Input Capacitance	C_{IN}		5					pF
Output Capacitance	C_{OUT}	Output Disabled	10					pF
Power Dissipation Capacitance*	C_{PD}							pF

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

† For AC switching test circuits and timing waveforms see section 2.

†† These parameters are measured with the internal output state of the storage register opposite to that of the bus input.



PACKAGE DIMENSIONS*T-90-20***1. PLASTIC PACKAGES****14-Pin Plastic DIP Units: mm****16-Pin Plastic DIP Units: mm****20-Pin Plastic DIP Units: mm****24-Pin Plastic DIP Units: mm**

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**SAMSUNG SEMICONDUCTOR**

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A-04

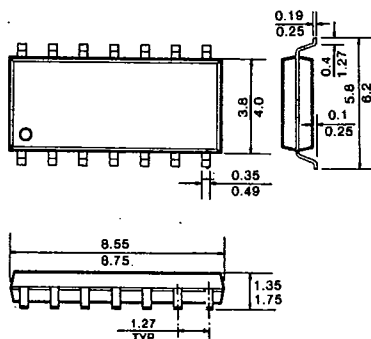
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PACKAGE DIMENSIONS

T-90-20

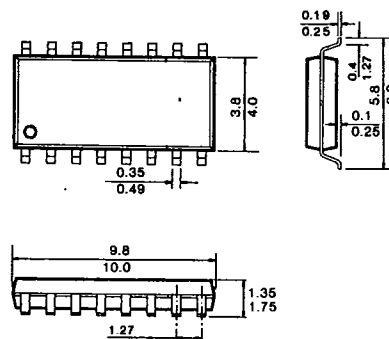
14-Pin SOP

Unit: mm



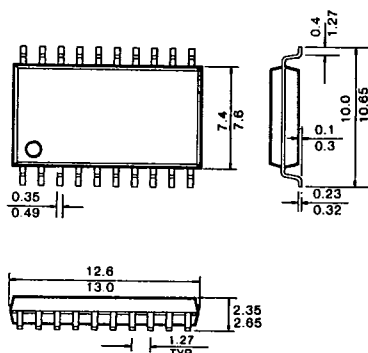
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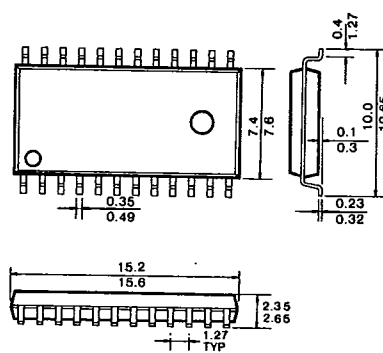
20-Pin SOP

Unit: mm



24-Pin SOP

Unit: mm



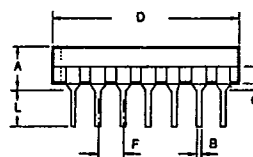
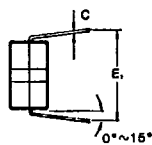
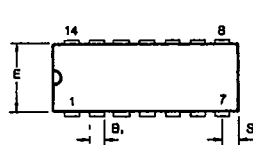
SAMSUNG SEMICONDUCTOR

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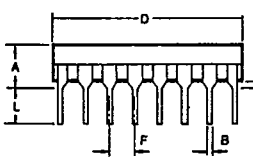
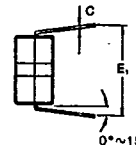
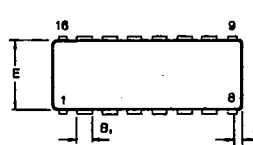
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PACKAGE DIMENSIONS

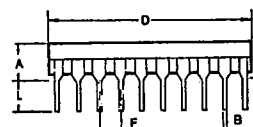
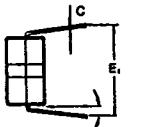
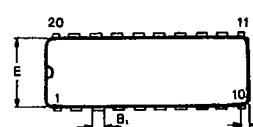
T-90-20

2. CERAMIC PACKAGES**14-Pin Ceramic DIP Units: mm**

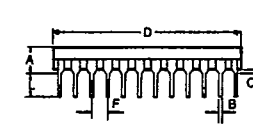
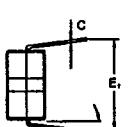
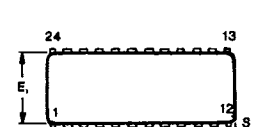
DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	18.16	19.56
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

16-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B ₁	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E ₁	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

20-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

24-Pin Ceramic DIP Units: mm

DIM	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B ₁	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E ₁	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93



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